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RESEARCH WORKSHOP ON CONDENSED MATTER PHYSICS
(21 June - 3 September 1993)

WORKING PARTY ON SMALL SEMICONDUCTOR STRUCTURES
(2 - 13 August 1993)

PERSISTENT CURRENT OF A WIGNER CRYSTAL-RING

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These are preliminary lecture notes, intended only for distribution to participants

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Persistent Current of a One-Dimensional Wigner Crystal-Ring.

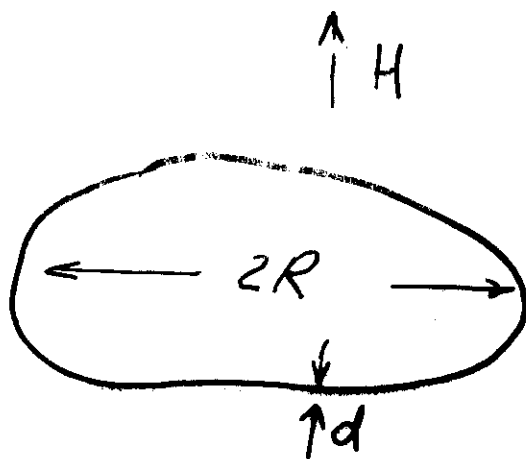
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Kharkov, Ukraine

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USA.

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Aharonov - Bohm Effect in Conductors



$$\Phi = H \cdot S; \quad \Phi_0 = \frac{h}{e}$$

$$R \approx 1 \mu\text{m}$$

$$d \approx 100 \text{ \AA}$$

M. Büttiker, Y. Imry, R. Landauer
Phys. Lett. 96A, 365 (1993)

Persistent Current

$$I(\Phi) = - \frac{\partial F}{\partial \Phi} \quad \text{— Periodic function of } \Phi \text{ with period } \Phi_0$$

$$I_{\text{max}}(\tau) \approx \frac{e}{\tau_c} \exp\left\{-\left(\frac{\tau}{\tau_c}\right)^n\right\}$$

1D - ring.

$$\tau_0 \approx \hbar / \epsilon_c \quad ; \quad n = \begin{cases} 1, & l \gg L \\ 0.5, & l \ll L \end{cases}$$

τ_c - circulation time

$$\tau_c \approx \begin{cases} L / v_F & l \gg L \\ L^2 / D & l \ll L \end{cases} \quad ; \quad D \approx \frac{v_F l}{3}$$

Diffusive and Ballistic Rings

I. Metallic rings

$d \gg \lambda_F$ Many transverse modes
(3-d ring)

$L \gg \ell$ Diffusive transport of electrons

$2B \cdot n^{1/3} \gg 1$ Ideal gas of electrons (mean field)

II. Gate-produced rings in 2-D semiconducting layers.

1. D. Mailly, C. Chapelier, A. Benoit
PRL, 80, 2020 (1998)

2. J. Liu, W.X. Gao, K. Ismail, K.Y. Lee, Y.H. Hong, S. Washburn
PRB (unpublished)

1. $d \approx \lambda_B$ (one or few modes of transverse motion; nearly 1-D ring)

2. $\ell > L$ Ballistic transport of electrons

3. $2B \cdot n^{1/2} \equiv \alpha^2 < 1$ (Electronic correlations should be important)

What is the role of interelectronic Coulomb correlations?

$$I_{\text{exp}}(T=0) \approx \frac{eV_F}{L} \quad \text{1-D ballistic ring. (free electrons)}$$

In a diffusive ring Coulomb interaction of electrons increase the persistent current $\downarrow$

1. V. Ambegaokar, U. Eckern
PR4, 65, 381 (1990)

2. A. Schmid, PR4, 66, 80, (1991)

conclusion ~~→~~ Coulomb interaction is not essential in semiconducting ring. =

Is this conclusion correct?

Strong Coulomb Correlations

$$\alpha^2 = \frac{2\phi}{a} \ll 1$$

$$2\phi \approx \frac{\epsilon_0 \hbar^2}{m e^2}$$

$\frac{E_{\text{kin}}}{E_{\text{coul}}} \approx \alpha^2 \ll 1 \Rightarrow$ Electrons form a Wigner Crystal

Persistent current is just a rotation of the Wigner Crystal as a whole



If we shift ^{the} crystal by period a during some time we produce the current which corresponds to the full rotation of a single electron. $\Rightarrow I = \frac{e v_F}{L}$

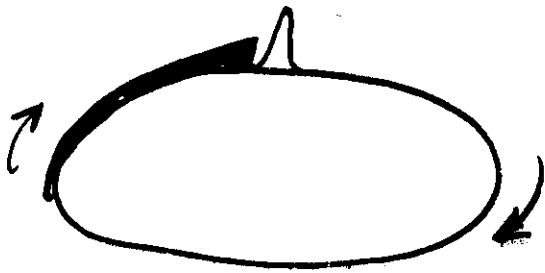
$$V_\phi \approx \frac{e}{mc} A = \frac{\hbar}{4m} \frac{\phi}{\phi_0} \quad \text{At } \phi = \phi_0 \quad V_\phi = \frac{\hbar}{4m}$$

$$E = M V_\phi^2 = \frac{1}{a} m V_\phi^2 = \frac{\hbar^2}{m a L} = \frac{\hbar v_F}{L}; \quad V_\phi = \frac{\hbar}{m a}$$

At $T \gtrsim M V_\phi^2 = T_0$ we destroy decompensation of clockwise and counterclockwise ~~in~~ rotations and current will disappear

$$T = \hbar v_F$$

Persistent Current in the WC Ring containing a Barrier.



A rotation of the WC
is accompanied with
a crystal deformation

U_{pin} - Pinning Energy

$U = ms^2 \frac{a}{L}$ - Deformation Energy

Strong Pinning

A. L. Hazen, P. Lee
PR 113, 1596 (1978)

$$\frac{U_{pin}}{U} \gg 1$$

Three steps of the rotation

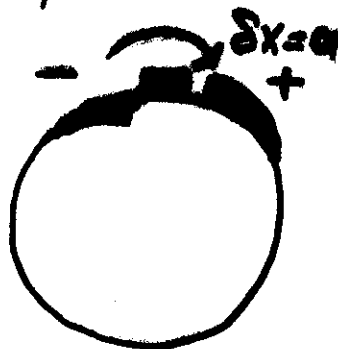
There are two parts of WC: 1) a pinned
part with size

$$l_0 = \frac{ms^2 a}{U_{pin}} \ll L$$

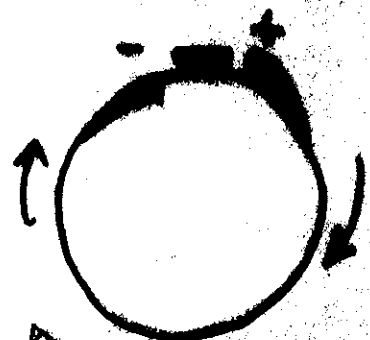
2) an unpinned part $\rightarrow (L - 2l_0)$



$\delta x = \frac{a}{2}$
rotation + deformation

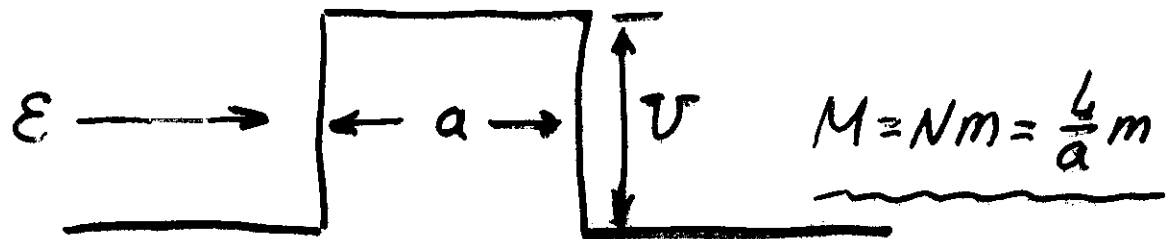


turning
through the barrier



$\delta x = a$
rotation + deformation

Tunneling through the elastic deformed configuration



$$U = ms^2 \frac{g}{L}; \quad E_0 = \frac{\hbar^2}{2Ma^2} = \frac{\hbar^2}{2mL^2} = T_0 \quad V_F = \frac{\hbar^2}{2mL^2}$$

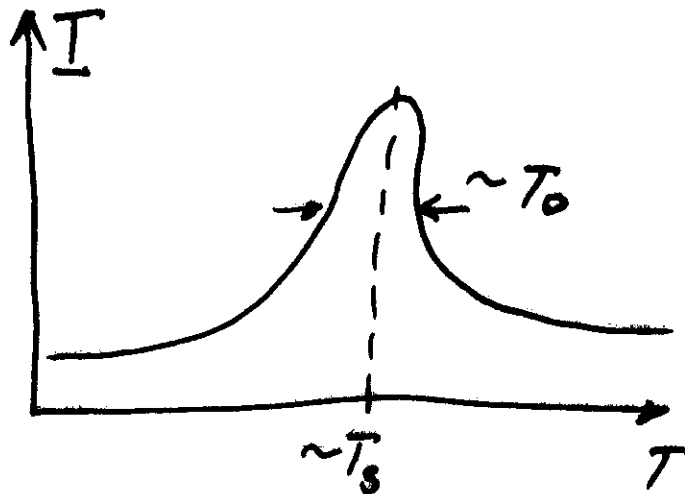
$$E_0/U = \left(\frac{V_F}{s}\right)^2 \equiv \alpha^2 \ll 1.$$

$$W(E, T) \approx \exp \left\{ -\frac{a}{\hbar} \sqrt{2M(U-E)} + \frac{E}{T} \right\}$$

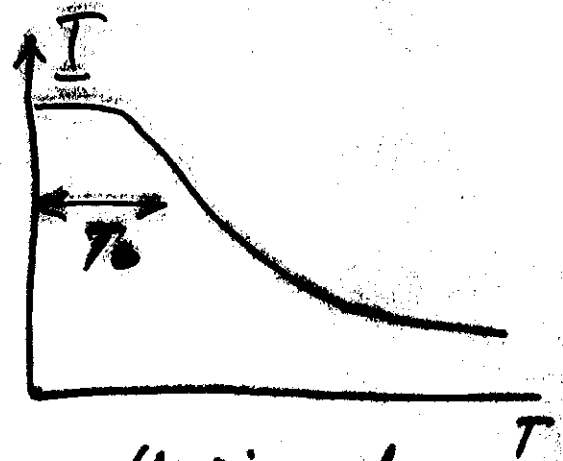
$$W(E_{\max}, T) \approx \exp \left\{ -\frac{U}{T} + \frac{T}{E_0} \right\}$$

$$T_{\max} = \sqrt{UE_0} = \frac{\hbar s}{2} \equiv T_S \gg T_0$$

$$\delta T \approx T_{\max} \left(\frac{T_{\max}}{U} \right)^{1/2} \ll T_{\max}$$

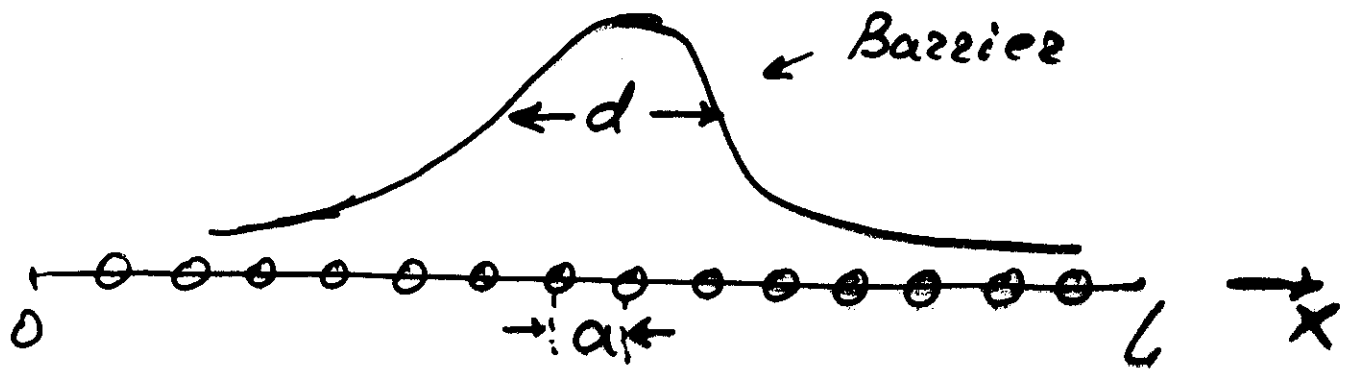


Pinned Crystal



Unpinned crystal

Formulation of the Problem



$$\underline{a \ll d \ll L}$$

We will use the longwavelength approximation.

Pinning Energy : $V(u)$

Displacement of electrons $u(x)$

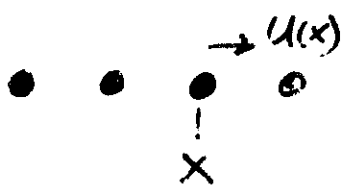
$V(u) = V(u+a)$ periodic function can be expanded in Fourier series

If $d \gg a$ we can use only first harmonics (others will be exponentially smaller)

$$V(u) = \text{Const} + V \cos \frac{2\pi u(x)}{a} \times \delta(x)$$

L.I. Glezerman, I.M. Ruzin, B.I. Shklovskii
PR B45, 8584 (1992)

Long wavelength Approximation



$$\varphi(x) = 2\pi \frac{u(x)}{a} \quad \text{Dimensionless displacement}$$

$$\mathcal{L} = \frac{ma^2}{8\pi^2} \{ \dot{\varphi}^2 - s^2 (\varphi')^2 \} - V_p \delta(x) \cos(\varphi)$$

s - sound velocity

$$\mathcal{L}_\varphi = \frac{\hbar}{L} \frac{\partial}{\partial \varphi_0} \dot{\varphi} \quad A_\varphi = \frac{\varphi}{L}; \quad \varphi_0 = \frac{\hbar}{e}$$

Free Energy

$$F = -T \ln \left\{ \int D\varphi \exp \left(- \frac{S_E[\varphi]}{\hbar} \right) \right\}$$

$$S_E(\varphi) = \int_{-\beta/2}^{\beta/2} d\tau \int_0^L dx \mathcal{L}[\varphi(\tau, x)] + i\pi n N \hbar$$

$$\varphi_n(\tau + \beta, x) = \varphi_n(\tau, x) + 2\pi n$$

$$\boxed{\mathcal{I} = - \frac{\partial F}{\partial \varphi}}$$

Quasiclassic limit

$$\alpha = \sqrt{\frac{2B}{a}} \ll 1.$$

We can use the saddle point approximation to calculate path integral.

Extreme trajectories we get from the equation.

$$\ddot{\varphi} + S^2 \varphi'' = \frac{8\pi^2}{mq^2} V_p \delta(x) \cos(\varphi)$$

$$\varphi(\tilde{z} + A_2, x) = \varphi(\tilde{z} - A_2, x) + 2\pi n$$

Persistent Current of WC with no Barrier.

$$\underline{V_p = 0}$$

$$\psi_n(x) = \frac{2\pi n}{\beta} x$$

By Calculation of the action of the extreme trajectory we can find

$$I_{wc} = (-1)^N 2I_0 \begin{cases} \arctan\left[\tan\left(\frac{I_0}{T}\right)\right], & T < T_0 \\ \frac{I_0}{T_0} e^{-\frac{\pi T}{T_0}} \sin\left(2\pi \frac{I_0}{T_0}\right), & T \geq T_0 \end{cases}$$

$$I_0 = \frac{eV_F}{L}; \quad T_0 = \frac{\hbar V_F}{L}$$

$$V_F = \hbar/m a$$

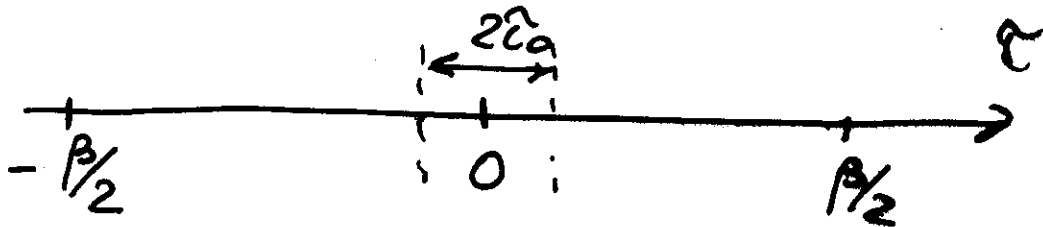
We got the same result as for free electron gas.

Persistent Current in the Case of a Strong Pinning.

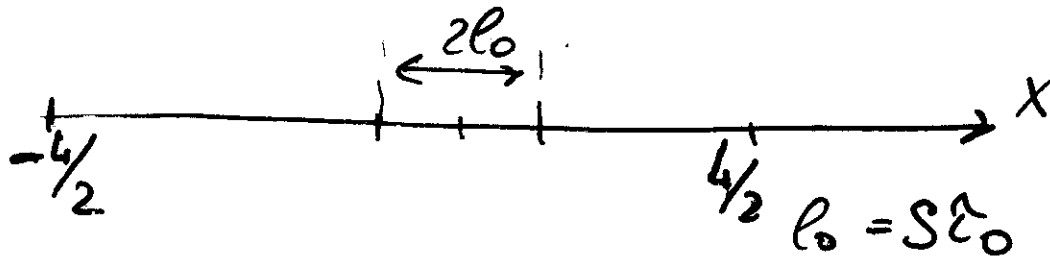
$$V_p \gg \alpha^{-1} \cdot T_S$$

$$\alpha^{-1} = \frac{S}{V_F}$$

$$T_S = \frac{1}{2} S / L$$



A.I. Larkin, P.A. Lee PR B18, 1596 (1978)



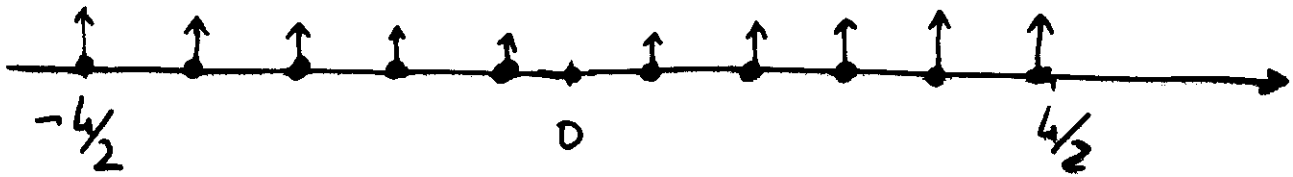
$$l_0 = \frac{m S^2 \hbar}{V_p} \ll L$$

For $|x| > l_0$; $|\tau| > \hat{\tau}_0$ we can use the free elasticity equation to find ^{the} trajectory part, corresponding to the elastic relaxation.

A)

$\uparrow \psi$

$-\frac{\beta}{2} < \xi < 0 (-\xi_0)$



B)

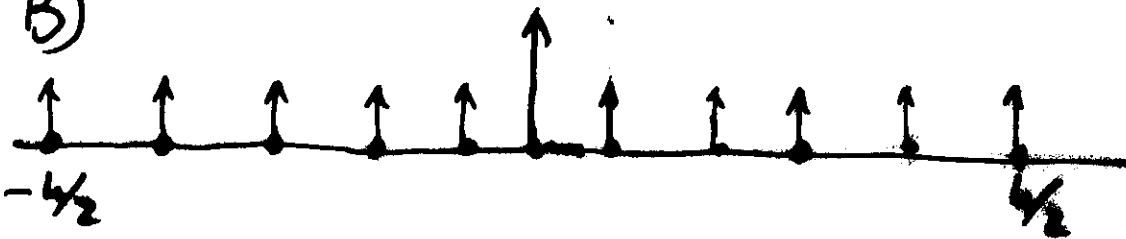
$\xi = -0 (-\xi_0)$

$\frac{\beta}{2}$



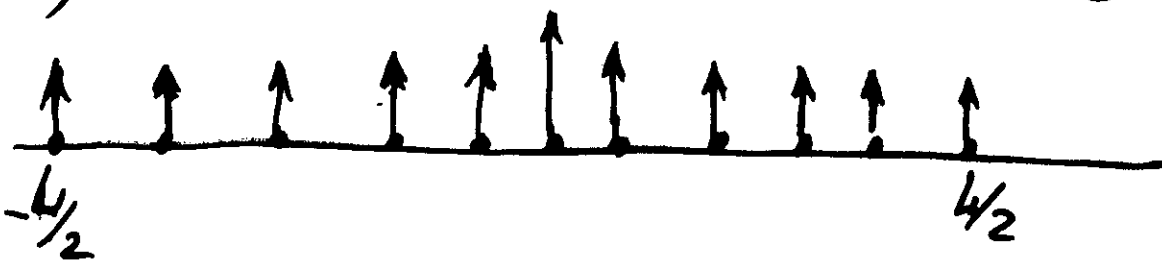
$\xi = +0 (+\xi_0)$

B)



C)

$(\xi_0) 0 < \xi < \frac{\beta}{2}$



Instanton solutions for elastic relaxation

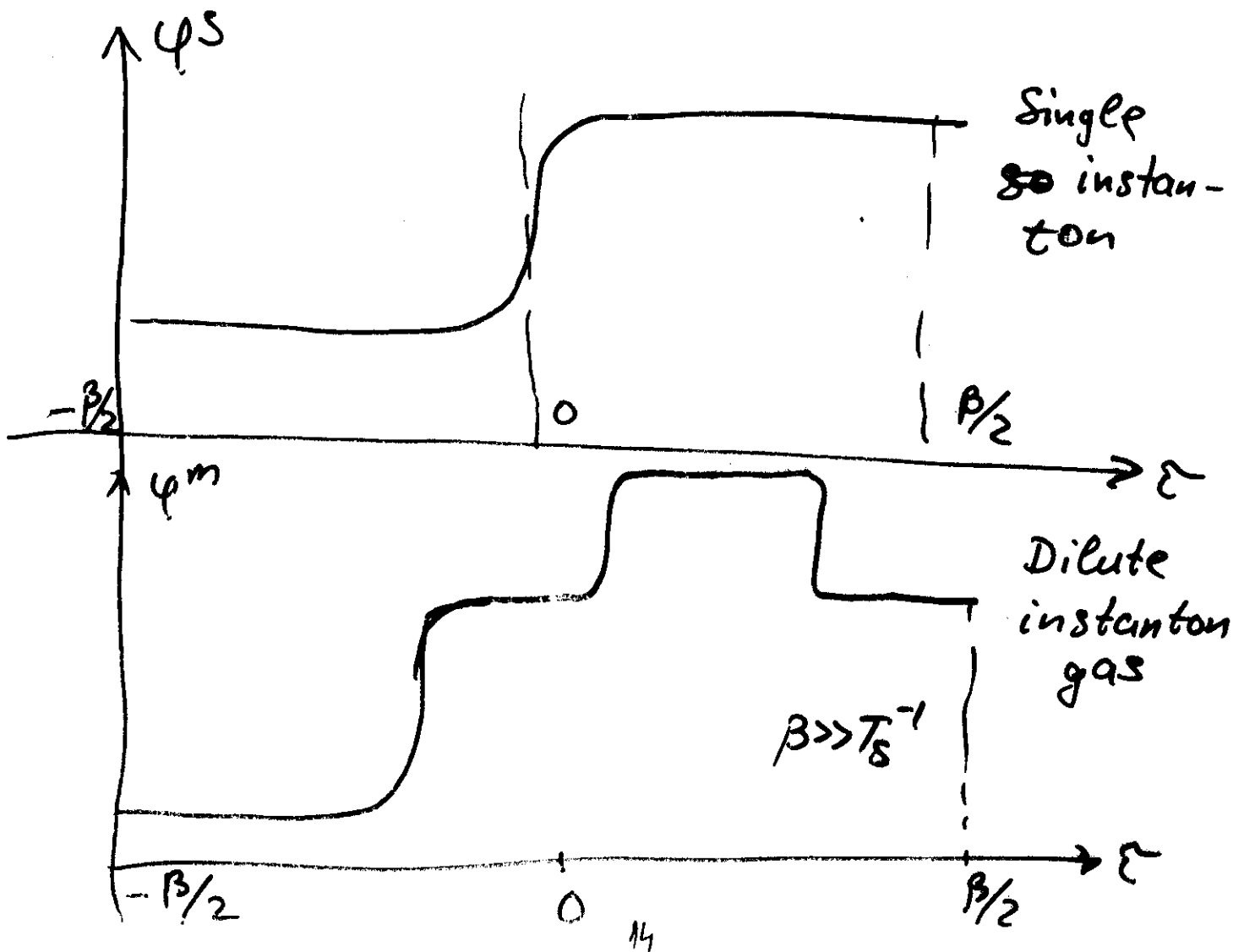
for $n = \pm 1$, $T \approx T_S$

$$\varphi_{\sigma}^s(x, \tau) = 2G \arctan \left[\coth \left(\frac{\pi |x|}{\hbar s \beta} \right) \tan \frac{\pi \hat{c}}{\hbar \beta} \right]$$

$$G = \pm 1$$

for $T \ll T_S$

$$\varphi_{\sigma}^{(m)} = \sum_e \varphi_{\sigma_e}^s(\tau - \tau_e) \quad \sigma = \sum_e \sigma_e = \pm 1$$



Permittivity Coefficient

$$S_{ext} = \int_{|t| > t_0} \int_{|x| > l_0} d\vec{r} \, L\{\psi_{ext}\} / t$$

$$I_{wc}(T=0) \approx (-1)^N \frac{es}{L} \left(\frac{T_s}{\alpha V_0} \right)^{1/\alpha} \sin(2\pi \varphi_0)$$

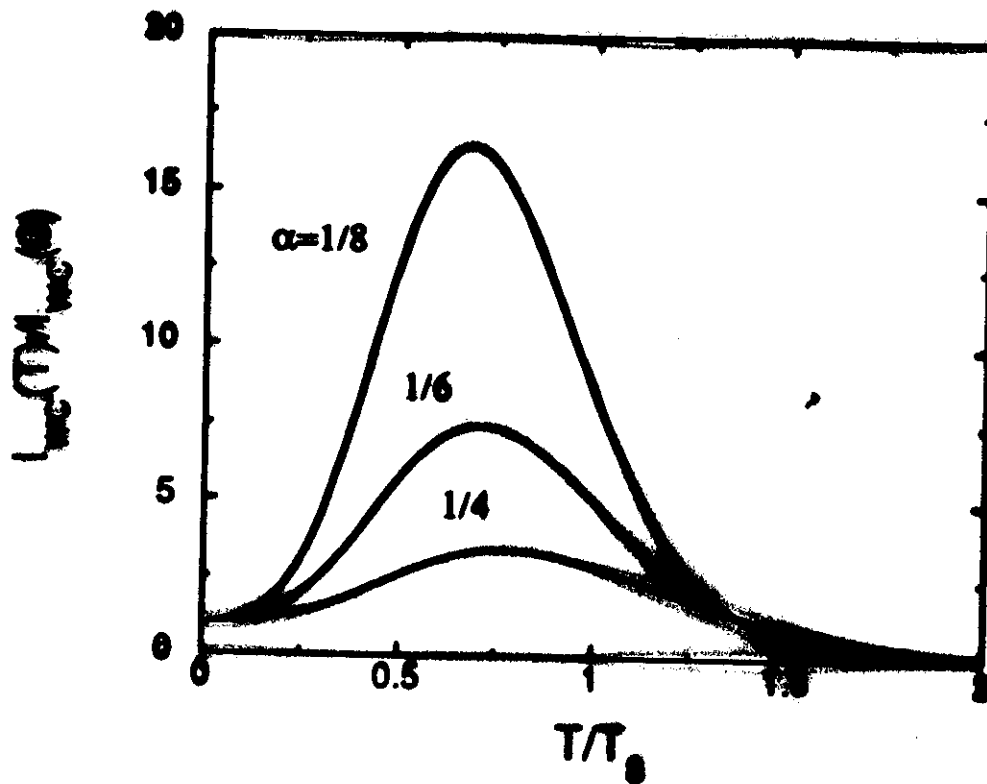
$$\frac{I_{wc}(T)}{I_{wc}(0)} = \frac{T}{T_s} \exp\left[\frac{1}{\alpha} f(T/T_s)\right] \quad T \ll \alpha V_0$$

$$f(x) = \frac{\pi}{2} x - \ln\left[\frac{\sinh(\pi x)}{x}\right]$$

$$I_{wc}(T=T_{max}) = \max I_{wc}$$

$$T_{max} = 0.5 T_s \quad \alpha \ll 1.$$

Figure 2.



Conclusions

- Persistent Current in a Ballistic 1-D Ring does not influenced by strong Coulomb correlations
- Incorporation of potential Barrier in a Ring results in qualitative change of the magnitude and temperature dependence of the persistent current
- Experiments with a gate controlled barrier can be used for detecting and investigation the properties of the Wigner Crystal.